

EAST Search History (z1pp.1) ~~48~~

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	1858	257/77	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/09/26 13:40
L2	251	257/78	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/09/26 13:40
L3	12	/183	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/09/26 13:40
L4	215956	"197"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/09/26 13:40
L5	375853	"198"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/09/26 13:40
L6	3413	((257/77) or (257/78) or (257/183) or (257/197) or (257/198) or (438/931)).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/09/26 14:16
L7	1	6 and (single adj ((crystal crystalline crystallinity monocrystal monocrystalline monocrystallinity mono-crystal mono-crystalline mono-crystallinity) near4 (si silicon))) and (single adj ((crystal crystalline crystallinity monocrystal monocrystalline monocrystallinity mono-crystal mono-crystalline mono-crystallinity))) near4 (sic silicon adj carbide) and (abrupt abruptly steep steeply slope sloping graded grading sloped drastic sudden drastically suddenly) and (oxygen "O. ₂ " O) near8 (density concentration abundance) near8 (silicon adj carbide silicon si sic) and (thickness thick) near4 (layer film)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/26 14:17

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L9	1	7 and (c carbon) near1 concentration	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/09/26 14:11
L10	3778	((257/77) or (257/78) or (257/183) or (257/197) or (257/198) or (257/616) or (438/931)).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/09/26 14:17
L11	1	10 and (single adj ((crystal crystalline crystallinity monocrystal monocystalline monocrystallinity mono-crystal mono-crystalline mono-crystallinity) near4 (si silicon))) and (single adj ((crystal crystalline crystallinity monocrystal monocystalline monocrystallinity mono-crystal mono-crystalline mono-crystallinity)) near4 (sic silicon adj carbide) and (abrupt abruptly steep steeply slope sloping graded grading sloped drastic sudden drastically suddenly) and (oxygen "O. ₂ " O) near8 (density concentration abundance) near8 (silicon adj carbide silicon si sic) and (thickness thick) near4 (layer film)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/26 14:26
L12	1	10 and (single adj ((crystal crystalline crystallinity monocrystal monocystalline monocrystallinity mono-crystal mono-crystalline mono-crystallinity) near4 (si silicon))) and (single adj ((crystal crystalline crystallinity monocrystal monocystalline monocrystallinity mono-crystal mono-crystalline mono-crystallinity)) near4 (sic silicon adj carbide) and (abrupt abruptly steep steeply slope sloping graded grading sloped drastic sudden drastically suddenly) and (oxygen "O. ₂ " O) near8 (density concentration abundance) near8 (silicon adj carbide silicon si sic) and (thickness thick) near4 (layer film) and transistor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/26 14:27

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L14	488	uhv-cvd	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/26 14:43
L15	1874	uhv-cvd.ti,ab,clm. (ultra adj high adj vacuum).ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/26 14:43
L16	156	uhv-cvd.ti,ab,clm. ((ultra adj high adj vacuum).ti,ab,clm. and cvd.ti, ab,clm.)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/26 14:44
L17	89	uhv-cvd.ti,ab,clm. ((ultra adj high adj vacuum).ti,ab,clm. and cvd.ti, ab,clm.) and silicon adj carbide	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/26 14:45
L27	532	(257/198).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/09/26 15:01
L28	71	27 and (sic silicon adj carbide)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/09/26 15:12
L29	29	27 and (sic silicon adj carbide) and (uhv-cvd oxygen O)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/26 15:19
L30	24	27 and (sic silicon adj carbide) and (uhv-cvd oxygen O) and (profile density graded grading abrupt steep sharp)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/26 15:28
L31	0	27 and (sic silicon adj carbide) and (uhv-cvd or ((carbon c) near4 profile concentration density)) and oxygen near4 (concentration density abundance)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/26 15:35
L32	3541	((257/77) or (257/197) or (257/198) or (257/616) or (257/183) or (438/931)).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/09/26 16:16

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L33	7	32 and (sic silicon adj carbide) and (silicon si) and ((uhv-cvd ultra adj high adj vacuum ultra-high-vacuum) near4 (cvd chamical adj vapo\$1or adj deposition) or ((abrupt steep\$2 sharp\$2) near4 (profile gradient graded increas\$3 decreas\$3))) and ("O" "O.sub."\$1 oxygen) near3 (content concentration density)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/26 16:16
L34	1	32 and (sic silicon adj carbide) and (silicon si) and ((uhv-cvd ultra adj high adj vacuum ultra-high-vacuum) near4 (cvd chamical adj vapo\$1or adj deposition) or ((abrupt steep\$2 sharp\$2) near4 (profile gradient graded increas\$3 decreas\$3))) and ("O" "O.sub."\$1 oxygen) near3 (content concentration density) and @ad<"20010421"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/26 15:54
L35	1	(silicon adj carbide sic).clm. and ((mono single) adj (crystal crystalline) (monocrystal monocrystalline) (mono-crystal mono-crystalline single-crystal single-crystalline)).clm. and ((c carbon) near4 (concentration density abundance)).clm. and (oxygen "O") near4 ("10.sup."\$3). clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/26 16:16
L36	0	(silicon adj carbide sic).clm. and ((mono single) adj (crystal crystalline) (monocrystal monocrystalline) (mono-crystal mono-crystalline single-crystal single-crystalline)).clm. and ((c carbon) near4 (concentration density abundance)).clm. and (oxygen "O") near4 ("10.sup."\$3). clm. and @ad<"20010421"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/26 16:15
L37	728	((257/613) or (257/616)).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/09/26 16:15

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L38	0	37 and (silicon adj carbide sic). clm. and ((mono single) adj (crystal crystalline) (monocrystal monocrystalline) (mono-crystal mono-crystalline single-crystal single-crystalline)).clm. and ((c carbon) near4 (concentration density abundance)).clm. and (oxygen "O") near4 ("10.sup."\$3). clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/26 16:16
L39	3794	((257/77) or (257/197) or (257/198) or (257/613) or (257/616) or (257/183) or (438/931)).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/09/26 16:16
L40	7	39 and (sic silicon adj carbide) and (silicon si) and ((uhv-cvd ultra adj high adj vacuum ultra-high-vacuum) near4 (cvd chamical adj vapo\$1or adj deposition) or ((abrupt steep\$2 sharp\$2) near4 (profile gradient graded increas\$3 decreas\$3)) and ("O" "O.sub."\$1 oxygen) near3 (content concentration density)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/26 16:21
L41	19	(("5780327") or ("5906951") or ("6723621") or ("6013134") or ("6096590") or ("6350993") or ("6251751") or ("6059895") or ("6425951") or ("6475072")).PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/09/26 16:26
L42	0	("jagganathan.in.").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/09/26 16:27
L43	0	("jagannathan.in.").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/09/26 16:27
L44	544	jagannathan.in.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/09/26 16:27
L45	38	(basanth near2 jagannathan).in.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/09/26 16:28

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L46	38	(basanth near2 jagannathan).in.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/26 16:39
L47	0	("711640.ap.753001.ap.908448.ap.").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/09/26 16:39
L48	17	"711640".ap. "753001".ap. "908448".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/26 16:49
L49	2	("5777364").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/09/26 16:53
L50	2	("5352912").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/09/26 16:53
S1	4	"775514".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/04/16 14:02
S2	6	(("6,285,064") or ("6,358,773") or ("6,368,888")).PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/03 22:06
S3	1	(US-20040161875-\$).did.	US-PGPUB	OR	OFF	2005/04/03 22:08
S4	10	(silicon adj carbide sic) near20 graded near20 buffer and single adj (crystalline crystal) near4 (silicon si)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/03 22:13
S5	2	(silicon adj carbide sic) near20 graded near20 buffer and single adj (crystalline crystal) near4 (silicon si) and (thick thickness) near10 buffer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/03 22:18

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S6	2	("6750119").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/03 22:18
S7	1	"5683934".PN.	USPAT; USOCR	OR	OFF	2005/04/03 22:19
S8	1	"5906680".PN.	USPAT; USOCR	OR	OFF	2005/04/03 22:19
S9	1	"6190975".PN.	USPAT; USOCR	OR	OFF	2005/04/03 22:20
S10	1	"20020160605".PN.	US-PGPUB	OR	OFF	2005/04/03 22:20
S11	155	junction near4 (sic silicon adj carbide) near4 (si silicon) and (monocrystalline single adj (crystal crystalline))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/04 09:50
S12	15	(US-20010015170-\$).did. or (US-6472594-\$ or US-6273950-\$ or US-6214107-\$ or US-6183857-\$ or US-5861324-\$ or US-5847418-\$ or US-5726440-\$ or US-5681402-\$ or US-5671914-\$ or US-5599403-\$ or US-5459089-\$ or US-5456762-\$ or US-5449923-\$).did. or (JP-62216364-\$).did.	US-PGPUB; USPAT; JPO	OR	OFF	2005/04/04 09:49
S13	144	S11 and (interface thick thickness abrupt sharp buffer)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/04 09:51
S14	14	S12 and (interface thick thickness abrupt sharp buffer)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/04 09:51
S15	7	S12 and (interface thick thickness abrupt sharp buffer) and ("SiC/Si" "Si/SiC")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/04 10:13
S16	3	(("5298452") or ("5906680")).PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/04 10:01

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S17	0	(257/77 and uhf-cvd and ("S/SiC""SiC/S")).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/04 10:02
S18	0	257/77 and uhf-cvd and ("S/SiC""SiC/S")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/04 10:02
S19	0	257/77 and uhf-cvd and ("S/SiC""SiC/S")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/04 10:02
S20	0	257/77 and uhf near1 cvd	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/04 10:03
S21	0	257/77 and uhf adj cvd	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/04 10:03
S22	0	257/77.ccls. and uhf adj cvd	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/04 10:03
S23	3	257/77.ccls. and uhf and cvd	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/04 10:03
S24	1260	((257/77) or (438/931)).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/29 07:26
S25	47	S24 and ("Si/SiC" "SiC/S" interface junction) near10 (abrupt sharp)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/04 10:24
S26	5	S24 and hbt and buffer and graded and (thick thickness thin)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/04 11:40

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S27	0	(single adj (crystalline crystal) monocrystalline) near3 (silicon "Si") near6 (silicon adj carbide "SiC") and graded near4 ("Si.sub. "\$3"C.sub."\$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/04 11:44
S28	363	(single adj (crystalline crystal) monocrystalline) near1 (silicon "Si") near2 substrate near6 (silicon adj carbide "SiC")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/04 11:45
S29	0	(single adj (crystalline crystal) monocrystalline) near1 (silicon "Si") near2 substrate near6 (silicon adj carbide "SiC") and (buffer graded) near4 ("Si.sub.xC.sub.1-x" "Si.sub.1-xC.sub.x")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/04 11:46
S30	0	(single adj (crystalline crystal) monocrystalline) near1 (silicon "Si") near2 substrate near6 (silicon adj carbide "SiC") and "Si.sub. "\$3"C.sub."\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/04 11:47
S31	363	(single adj (crystalline crystal) monocrystalline) near1 (silicon "Si") near2 substrate near6 (silicon adj carbide "SiC")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/04 11:48
S32	179	(single adj (crystalline crystal) monocrystalline) near1 (silicon "Si") near2 substrate near6 (silicon adj carbide "SiC") not (silicon adj carbide adj substrate)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/04 12:19
S33	10	(("5,906,680") or ("6,190,975") or ("20010160605") or ("5,683,934") or ("20020016085") or ("6,306, 211")).PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/04 12:24
S34	10	(("5,906,680") or ("6,190,975") or ("5,683,934") or ("20020016085") or ("6,306,211")).PN. or (2001/0160605).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/04 12:24
S35	0	("20010160605").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/04 12:25

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S36	0	(2001/0160605).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/04 12:25
S37	85	kanazawa.in. and "200210"\$2.pd.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/04 12:26
S38	273	kanazawa.in. and silicon	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/04 12:26
S39	31	kanazawa.in. and silicon	US-PGPUB	OR	OFF	2005/04/04 12:31
S40	26	kanazawa.in. and silicon and substrate	US-PGPUB	OR	OFF	2005/04/04 12:26
S41	0	@pd="200210"\$2 and kanazawa.in.	US-PGPUB	OR	OFF	2005/04/04 12:31
S42	202	kanazawa.in.	US-PGPUB	OR	OFF	2005/04/04 12:32
S43	4	suemitsu.in. and sic adj film	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/04 12:53
S44	0	suemitsu.in. and nakazaka.in.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/04 12:53
S45	4	suemitsu.in. and nakazawa.in.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/04 12:59
S46	0	("20010160605").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/04 12:58
S47	2	("2001160605").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/04 12:58

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S48	15481	nakazawa.in.	US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/04 12:59
S49	125	nakazawa.in. and "200210"\$2.pd,	US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/04 13:01
S50	187	nakazawa.in. and substrate	US-PGPUB	OR	OFF	2005/04/04 13:57
S51	0	(2004/0161875).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/04 13:57
S52	2	("20040161875").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/04 13:58
S53	2	("200?0161875").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/04 13:58
S54	0	("20010160605").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/04 13:59
S55	0	("(monocrystallinesingleadjcrystal) near2(siliconSi)and(carbonC)and(c oncentrationprofile)").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/27 10:25
S56	8580	(monocrystalline single adj crystal) near2 (silicon Si) and (carbon C) and (concentration profile) and boron	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/27 10:26
S57	1322	(monocrystalline single adj crystal) near2 (silicon Si) and (carbon C) and (concentration profile) and boron near5 (barrier diffusion)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/27 10:26

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S58	85	(monocrystalline single adj crystal) near2 (silicon Si) and (carbon C) and (concentration profile) and boron near5 (barrier diffusion) and (hbt heterojunction adj bipolar adj transistor)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/27 10:27
S59	456	gated adj diode	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/27 12:14
S60	73	gated adj diode.ti.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/27 12:15
S61	3	"751714".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/27 12:16
S62	46	boron near1 diffusion and (silicon adj carbide SiC) and concentration near3 profile and (silicon Si) near3 substrate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/28 08:55
S63	0	intrinsic adj buffer near3 (silicon si) near6 (crystalline monocrystalline single adj crystal) and hbt	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/28 08:57
S64	188	buffer near3 (silicon si) near6 (crystalline monocrystalline single adj crystal) and hbt	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/28 09:23
S65	0	collector near4 lattice and S64	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/28 09:23
S66	0	collector near10 lattice and S64	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/28 09:23

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S67	8	collector near10 lattice and S62	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/28 10:23
S68	27	(single adj crystalline monocrystalline) near2 emitter and hbt	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/28 10:32
S69	1	(single adj crystalline monocrystalline) near2 emitter near5 (mobility conductivity resistivity) and hbt	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/28 11:05
S70	13	(single adj crystalline monocrystalline) near2 emitter near5 (mobility conductivity resistivity)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/28 11:05
S71	88	polycrystalline near3 emitter and hbt	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/28 12:44
S72	27	polycrystalline near3 emitter and hbt and (carbide SiC)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/28 12:45
S73	1	polycrystalline near3 (carbide SiC) near4 emitter and hbt and (carbide SiC)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/28 12:46
S74	1	polycrystalline near3 (carbide SiC) near4 emitter and hbt	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/28 12:46
S75	2	("6137120").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/28 13:09
S76	95	fang.in. and emitter	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/28 13:10

EAST Search History

S77	5	(("5,906,680") or ("6,190,975") or ("20010160605") or ("5,683,934") or ("20020016085") or ("6,306,211")).PN.	US-PGPUB; USPAT	OR	OFF	2005/04/29 07:11
S78	59	(US-20010015170-\$ or US-20020016085-\$ or US-20020094658-\$ or US-20020102862-\$ or US-20020124793-\$ or US-20020158311-\$ or US-20020158313-\$ or US-20020160605-\$ or US-20020182423-\$ or US-20020192918-\$ or US-20030054601-\$ or US-20040089918-\$ or US-20040161875-\$ or US-20040195655-\$ or US-20040198010-\$ or US-20040217430-\$ or US-20050006663-\$ or US-20050023642-\$ or US-20050051798-\$ or US-20050064645-\$ or US-20050082571-\$).did. or (US-5296258-\$ or US-5298452-\$ or US-5449923-\$ or US-5456762-\$ or US-5459089-\$ or US-5599403-\$ or US-5670414-\$ or US-5671914-\$ or US-5681402-\$ or US-5683934-\$ or US-5726440-\$ or US-5847418-\$ or US-5861324-\$ or US-5906680-\$ or US-6064081-\$ or US-6183857-\$ or US-6190975-\$ or US-6214107-\$ or US-6273950-\$ or US-6285064-\$ or US-6306211-\$ or US-6358773-\$ or US-6362065-\$ or US-6368888-\$ or US-6472594-\$ or US-6552375-\$).did. or (US-6673662-\$ or US-6750119-\$).did. or (JP-62216364-\$).did. or (DE-3777507-\$ or EP-703628-\$ or EP-829908-\$ or EP-908984-\$ or EP-1039512-\$ or US-20020016085-\$ or US-6285064-\$ or US-6358773-\$ or US-20020102862-\$).did.	US-PGPUB; USPAT; JPO; DERWENT	OR	OFF	2005/04/29 07:14
S79	0	("2andkanazawa.in.").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/29 07:14

EAST Search History

S80	0	S78 and kanazawa.in.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/29 07:15
S81	2	S78 and nakazawa.in.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/29 07:15
S82	2120	((257/77) or (257/183) or (257/197) or (257/198) or (438/931)).CCLS.	US-PGPUB; USPAT	OR	OFF	2005/04/29 08:04
S83	355	S82 and silicon adj carbide and boron	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/29 07:31
S84	10	S82 and silicon adj carbide and boron and (uhv ultra adj "high" adj vacuum)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/29 08:05
S85	2300	((257/77) or (257/78) or (257/183) or (257/197) or (257/198) or (438/931)).CCLS.	US-PGPUB; USPAT	OR	OFF	2005/04/29 08:04
S86	180	S85 NOT S82	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/29 08:05
S87	0	S86 and silicon adj carbide and boron and (uhv ultra adj "high" adj vacuum)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/29 08:05
S88	4	"775514".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/24 16:36
S89	2	("6552375").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/24 16:54

EAST Search History

S90	0	laser adj melting near4 sic	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/24 16:54
S91	222	mbe near4 sic	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/24 17:00
S92	121	lattice adj constant near4 sic	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/24 17:00
S93	35	lattice adj constant near1 sic	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/24 17:15
S94	3	laser adj melting.ti. and (sic silicon adj carbide silicon adj germanium sige)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/24 17:32
S95	12	(("5906680") or ("6190975") or ("5693934") or ("6306211") or ("20020160605") or ("20020016085")).PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/24 17:33
S96	12	((("5906680") or ("6190975") or ("5683934") or ("6306211") or ("20020160605") or ("20020016085"))).PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/24 19:50
S97	2418	((257/77) or (257/78) or (257/183) or (257/197) or (257/198) or (438/931)).CCLS.	US-PGPUB; USPAT	OR	OFF	2005/09/24 19:50
S98	1	S97 and (single adj crystalline monocrystal monocrystalline) near4 (Si silicon).ti,ab,clm. and (silicon adj carbide Sic).ti,ab,clm. and oxygen near4 (concentration content density).ti,ab,clm. and interface.ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/24 20:02

EAST Search History

S99	4	(single adj crystalline monocrystal monocrystalline) near4 (Si silicon).ti,ab,clm. and (silicon adj carbide Sic).ti,ab,clm. and oxygen near4 (concentration content density).ti,ab,clm. and interface.ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/24 20:09
S10 0	226	(single adj crystalline monocrystal monocrystalline) near4 (Si silicon) and (silicon adj carbide Sic) and oxygen near4 (concentration content density) and interface	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/24 20:10
S10 1	4	(single adj crystalline monocrystal monocrystalline) near4 (Si silicon).ti,ab,clm. and (silicon adj carbide Sic).ti,ab,clm. and oxygen near4 (concentration content density).ti,ab,clm. and interface.ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/24 20:09
S10 2	190	(single adj crystalline monocrystal monocrystalline) near4 (Si silicon) and (silicon adj carbide Sic) and oxygen near2 (concentration content density) and interface	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/24 20:25
S10 3	2	("5929259").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/24 20:19
S10 4	60	(single adj crystalline monocrystal monocrystalline) near4 (Si silicon) and (silicon adj carbide Sic) and oxygen near2 (concentration content density) and interface and (dopant doping) near2 (concentration density)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/24 20:29
S10 5	3	(single adj crystalline monocrystal monocrystalline) near4 (Si silicon) and (silicon adj carbide Sic) and oxygen near2 (concentration content density) and interface and (dopant doping) near2 (concentration density) near6 (silicon adj carbide sic)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/24 20:29
S10 6	0	"5298254".pn. and UHV-CVD	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/04/16 14:06

EAST Search History

S10 7	2	"5298254".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/04/16 14:07
S10 8	2	"5298452".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/04/16 14:26
S10 9	0	S108 and (single adj crystal single adj crystalline monocrystal monocrystalline) near4 (SiC silicon adj carbide)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/04/16 14:27
S11 0	0	S108 and (SiC silicon adj carbide)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/04/16 14:27
S11 1	1	(US-20040161875-\$).did.	US-PGPUB	OR	OFF	2006/04/16 14:28
S11 3	2	"6552375".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/04/16 14:48
S11 4	0	S113 and (SiC silicon adj carbide) near4 (single monocrystal monocrystalline)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/04/16 14:40
S11 5	26	vpe near4 (single adj crystal\$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/04/16 14:48
S11 6	7	vpe near4 (single adj crystal\$4) near4 sic	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/04/16 14:56
S11 7	26	vpe near4 (single adj crystal\$4)"ti, ab,clm."	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/04/16 14:56

EAST Search History

S11 8	7	vpe near4 (single adj crystal\$4).ti, ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/04/16 16:02
S11 9	2316	shibahara.in.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/04/16 16:02
S12 0	0	shibahára.in. and step-controlled	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/04/16 16:02
S12 1	7	shibahara.in. and sic	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/04/16 16:14
S12 2	0	vpe near4 single adj crystal near4 sic	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/04/16 16:14
S12 3	7	vpe near4 (single adj crystal\$3) near4 sic	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/04/16 16:41
S12 4	25	(diffusion adj barrier) near4 (single adj crystal\$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/04/16 17:22
S12 5	3294	((257/77) or (257/78) or (257/183) or (257/197) or (257/198) or (438/931)).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/04/16 17:22
S12 6	1	S125 and abrupt near2 (junction interface).ti,ab,clm. and carbon near2 (density concentration ratio abundance).ti,ab,clm. and (monocrystal single adj crystal crystalline monocrystalline mon adj crystalline) near4 (silicon adj carbide SiC).ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/16 17:25

EAST Search History

S12 7	3	"6552375"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/09/21 09:22
S12 8	8	"144786".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/09/21 10:46
S12 9	0	(uhf-cvd (uhf adj cvd) ultra adj "high" adj frequency) near3 (cvd chemical adj vapo\$1r adj deposition) and (silicon si) and (silicon adj carbide sic)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/21 10:49
S13 0	3	(uhf-cvd (uhf adj cvd) ultra adj "high" adj frequency) near3 (cvd chemical adj vapo\$1r adj deposition)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/21 10:55
S13 1	3	(uhf-cvd (uhf adj cvd)) ((ultra adj "high" adj frequency) near3 (cvd chemical adj vapo\$1r adj deposition))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/21 10:57
S13 2	13577	(uhf-cvd (uhf adj cvd)) (ecr (ultra adj "high" adj frequency) near3 (cvd chemical adj vapo\$1r adj deposition))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/21 10:57
S13 3	33	(uhf-cvd uhf-ecr (uhf adj cvd)) ((ultra adj "high" adj frequency) near3 (cvd chemical adj vapo\$1r adj deposition))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/21 10:59
S13 4	4	(uhf-cvd (uhf adj cvd)) (((ultra adj "high" adj frequency) uhf) near3 (cvd chemical adj vapo\$1r adj deposition))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/21 11:02
S13 5	6	oxygen adj (concenteration impurity) near6 (sic silicon adj carbide)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/21 11:03
S13 6	40	oxygen adj (concentration impurity) near6 (sic silicon adj carbide)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/21 11:06

EAST Search History

S13 7	2	("6750119").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/09/21 11:12
S13 8	835	diffusion adj (constant rate coefficient) near3 (carbon C)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/21 11:13
S13 9	62	diffusion adj (constant rate coefficient) near4 (carbon C) near4 (silicon Si)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/21 13:19
S14 0	3	"6906680".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/21 13:19
S14 1	2	"5906680".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/21 13:59
S14 2	1	"5906680".pn. and abrupt	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/21 14:00
S14 3	1	"5906680".pn. and abrupt and thick\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/21 16:33

inv. name search. (15 pp.)

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Time: 16:38:11

PALM INTRANET

Inventor Name Search Result

Your Search was:

Last Name = JAGANNATHAN

First Name = BASANTH

Application#	Patent#	Status	Date Filed	Title	Inventor Name
<u>09633857</u>	6881259	150	08/07/2000	IN-SITU MONITORING AND CONTROL OF GERMANIUM PROFILE IN SILICON-GERMANIUM ALLOY FILMS AND TEMPERATURE MONITORING DURING DEPOSITION OF SILICON FILMS	JAGANNATHAN, BASANTH
<u>09683088</u>	6875279	150	11/16/2001	SINGLE REACTOR, MULTI-PRESSURE CHEMICAL VAPOR DEPOSITION FOR SEMICONDUCTOR DEVICES	JAGANNATHAN, BASANTH
<u>09683983</u>	6744079	150	03/08/2002	OPTIMIZED BLOCKING IMPURITY PLACEMENT FOR SIGE HBTS	JAGANNATHAN, BASANTH
<u>09774126</u>	6426265	150	01/30/2001	INCORPORATION OF CARBON IN SILICON/SILICON GERMANIUM EPITAXIAL LAYER TO ENHANCE YIELD FOR SI-GE BIPOLAR TECHNOLOGY	JAGANNATHAN, BASANTH
<u>09811859</u>	6506656	150	03/19/2001	STEPPED COLLECTOR IMPLANT AND METHOD FOR FABRICATION	JAGANNATHAN, BASANTH
<u>09822587</u>	6660607	150	03/30/2001	METHOD FOR FABRICATING HETEROJUNCTION BIPOLAR TRANSISTORS	JAGANNATHAN, BASANTH
<u>09838892</u>	6750119	150	04/20/2001	EPITAXIAL AND POLYCRYSTALLINE GROWTH OF Si _{1-X} -Ge _X AND Si _{1-Y} Ge _Y ALLOY LAYERS ON Si BY UHV-CVD	JAGANNATHAN, BASANTH
<u>09843783</u>	6780735	150	04/30/2001	METHOD TO INCREASE CARBON AND BORON DOPING CONCENTRATIONS IN Si AND	JAGANNATHAN, BASANTH

SIGE FILMS					
09885792	Not Issued	161	06/20/2001	Non-self-aligned SiGe heterojunction bipolar transistor	JAGANNATHAN, BASANTH
09962738	6927476	150	09/25/2001	BIPOLAR DEVICE HAVING SHALLOW JUNCTION RAISED EXTRINSIC BASE AND METHOD FOR MAKING THE SAME	JAGANNATHAN, BASANTH
10047975	6656809	150	01/15/2002	METHOD TO FABRICATE SIGE HBTS WITH CONTROLLED CURRENT GAIN AND IMPROVED BREAKDOWN VOLTAGE CHARACTERISTICS	JAGANNATHAN, BASANTH
10122857	6815802	150	04/15/2002	INCORPORATION OF CARBON IN SILICON/SILICON GERMANIUM EPITAXIAL LAYER TO ENHANCE YIELD FOR SI-GE BIPOLAR TECHNOLOGY	JAGANNATHAN, BASANTH
10249563	6780695	150	04/18/2003	BICMOS INTEGRATION SCHEME WITH RAISED EXTRINSIC BASE	JAGANNATHAN, BASANTH
10316211	6858532	150	12/10/2002	LOW DEFECT PRE-EMITTER AND PRE-BASE OXIDE ETCH FOR BIPOLAR TRANSISTORS AND RELATED TOOLING	JAGANNATHAN, BASANTH
10676171	6787427	150	10/01/2003	METHOD TO FABRICATE SIGE HBTS WITH CONTROLLED CURRENT GAIN AND IMPROVED BREAKDOWN VOLTAGE CHARACTERISTICS	JAGANNATHAN, BASANTH
10711640 N.D.P.	Not Issued	61	09/29/2004	STRUCTURE AND LAYOUT OF A FET PRIME CELL	JAGANNATHAN, BASANTH
10753001 Q.C.	Not Issued	161	01/07/2004	Optimized blocking impurity placement for SiGe HBTs	JAGANNATHAN, BASANTH
10775514	Not Issued	71	02/10/2004	Epitaxial and polycrystalline growth of Si _{1-x-y} Ge _x C _y and Si _{1-y} C _y alloy layers on Si by UHV-CVD	JAGANNATHAN, BASANTH
10775515 N.D.P. (all)	6908866	150	02/10/2004	EPITAXIAL AND POLYCRYSTALLINE GROWTH OF SI _{1-X-Y} GE _X C _Y AND SI _{1-Y} C _Y ALLOY LAYERS ON SI BY UHV-CVD	JAGANNATHAN, BASANTH
10908448 N.D.P.	Not Issued	71	05/12/2005	STRUCTURE AND METHOD OF MAKING A FIELD EFFECT TRANSISTOR HAVING AN ASYMMETRICALLY STRESSED	JAGANNATHAN, BASANTH

				CHANNEL REGION	
<u>10953378</u> <i>N, D P (all.)</i>	Not Issued	93	09/29/2004	INCORPORATION OF CARBON IN SILICON/SILICON GERMANTUM EPITAXIAL LAYER TO ENHANCE YIELD FOR SI-GE BIPOLAR TECHNOLOGY	JAGANNATHAN, BASANTH
<u>11057176</u> <i>N, D P.</i>	Not Issued	30	02/15/2005	Single reactor, multi-pressure chemical vapor deposition for semiconductor devices	JAGANNATHAN, BASANTH

Inventor Search Completed: No Records to Display.

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PALM INTRANET
Inventor Name Search Result

Your Search was:

Last Name = CHU

First Name = JACK OON

Application#	Patent#	Status	Date Filed	Title	Inventor Name
<u>08840741</u>	<u>5780327</u>	150	04/16/1997	VERTICAL DOUBLE-GATE FIELD EFFECT TRANSISTOR	CHU, JACK OON
<u>08846605</u>	<u>5906951</u>	150	04/30/1997	STRAINED SI/SIGE LAYERS ON INSULATOR	CHU, JACK OON
<u>08885611</u>	<u>6723621</u>	150	06/30/1997	ABRUPT DELTA-LIKE DOPING IN SI AND SIGE FILMS BY UHV-CVD	CHU, JACK OON
<u>09025889</u>	<u>6013134</u>	150	02/18/1998	ADVANCE INTEGRATED CHEMICAL VAPOR DEPOSITION (AICVD) FOR SEMICONDUCTOR DEVICES	CHU, JACK OON
<u>09099978</u>	Not Issued	161	06/19/1998	SI/SIGE OPTOELECTRONIC INTEGRATED CIRCUITS	CHU, JACK OON
<u>09107738</u>	<u>6096590</u>	150	06/30/1998	SCALABLE MOS FIELD EFFECT TRANSISTOR	CHU, JACK OON
<u>09267323</u>	<u>6350993</u>	150	03/12/1999	HIGH SPEED COMPOSITE P-CHANNEL SI/SIGE HETEROSTRUCTURE FOR FIELD EFFECT DEVICES	CHU, JACK OON
<u>09290778</u>	<u>6251751</u>	150	04/13/1999	BULK AND STRAINED SILICON ON INSULATOR USING LOCAL SELECTIVE OXIDATION	CHU, JACK OON
<u>09311468</u>	<u>6059895</u>	150	05/13/1999	STRAINED SI/SIGE LAYERS ON INSULATOR	CHU, JACK OON
<u>09369995</u>	<u>6425951</u>	150	08/06/1999	ADVANCE INTEGRATED CHEMICAL VAPOR DEPOSITION (AICVD) FOR SEMICONDUCTOR	CHU, JACK OON
<u>09675841</u>	<u>6475072</u>	150	09/29/2000	METHOD OF WAFER SMOOTHING FOR BONDING USING CHEMO-MECHANICAL POLISHING (CMP)	CHU, JACK OON
<u>11065816</u>	Not Issued	30	02/25/2005	High performance FET devices and methods thereof	CHU, JACK OON

Inventor Search Completed: No Records to Display.

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	CHU	JACK OON	

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Inventor Name Search Result

Your Search was:

Last Name = GRILL

First Name = ALFRED

Application#	Patent#	Status	Date Filed	Title	Inventor Name
<u>07504496</u>	<u>5031029</u>	250	04/04/1990	COPPER DEVICE AND USE THEREOF WITH SEMICONDUCTOR DEVICES	GRILL, ALFRED
<u>07634671</u>	<u>5159508</u>	150	12/27/1990	MAGNETIC HEAD SLIDER HAVING A PROTECTIVE COATING THEREIN	GRILL, ALFRED
<u>07785634</u>	<u>5155657</u>	250	10/31/1991	HIGH AREA CAPACITOR FORMATION USING MATERIAL DEPENDENT ETCHING	GRILL, ALFRED
<u>07854187</u>	Not Issued	166	03/20/1992	METHOD AND APPARATUS FOR FILLING HIGH ASPECT RATIO PATTERNS WITH METAL	GRILL, ALFRED
<u>07868371</u>	<u>5241131</u>	250	04/14/1992	EROSION/CORROSION RESISTANT DIAPHRAGM	GRILL, ALFRED
<u>07877334</u>	<u>5294518</u>	250	05/01/1992	AMORPHOUS WRITE-READ OPTICAL STORAGE MEMORY	GRILL, ALFRED
<u>07951924</u>	<u>5302266</u>	250	09/25/1992	METHOD AND APPARATUS FOR FILING HIGH ASPECT PATTERNS WITH METAL	GRILL, ALFRED
<u>08144907</u>	Not Issued	166	10/28/1993	DIAMOND-LIKE CARBON WRITE-READ OPTICAL STORAGE MEMORY	GRILL, ALFRED
<u>08236600</u>	Not Issued	161	04/29/1994	ELECTRODE STRUCTURE FOR CAPACITOR WITH HIGH DIELECTRIC CONSTANT MATERIALS	GRILL, ALFRED
<u>08257396</u>	<u>5416042</u>	150	06/09/1994	METHOD OF FABRICATING STORAGE CAPACITORS USING HIGH DIELECTRIC CONSTANT MATERIALS	GRILL, ALFRED
<u>08273689</u>	<u>5559367</u>	150	07/12/1994	DIAMOND-LIKE CARBON FOR USE IN VLSI AND ULSI INTERCONNECT SYSTEMS	GRILL, ALFRED

<u>08333405</u>	5462784	150	11/02/1994	FLUORINATED DIAMOND-LIKE CARBON PROTECTIVE COATING FOR MAGNETIC RECORDING MEDIA DEVICES	GRILL, ALFRED
<u>08346436</u>	5461536	250	11/29/1994	STORAGE CAPACITORS USING HIGH DIELECTRIC CONSTANT MATERIALS	GRILL, ALFRED
<u>08350249</u>	5440507	150	12/06/1994	DIAMOND-LIKE CARBON WRITE-READ OPTICAL STORAGE MEMORY	GRILL, ALFRED
<u>08371627</u>	5576579	150	01/12/1995	TASIN OXYGEN DIFFUSION BARRIER IN MULTILAYER STRUCTURES	GRILL, ALFRED
<u>08372633</u>	5625233	250	01/13/1995	THIN FILM MULTI-LAYER OXYGEN DIFFUSION BARRIER CONSISTING OF REFRACTORY METAL, REFRACTORY ALUMINIDE, AND ALUMINUM OXIDE	GRILL, ALFRED
<u>08465054</u>	5639316	150	06/06/1995	THIN FILM MULTI-LAYER OXYGEN DIFFUSION BARRIER CONSISTING OF ALUMINUM ON REFRACTORY METAL	GRILL, ALFRED
<u>08474616</u>	5663854	150	06/07/1995	PREBENT CERAMIC SUSPENSION	GRILL, ALFRED
<u>08483682</u>	5674355	250	06/07/1995	DIAMOND-LIKE CARBON FOR USE IN VLSI AND ULSI INTERCONNECT SYSTEMS	GRILL, ALFRED
<u>08537497</u>	5674638	250	10/02/1995	FLUORINATED DIAMOND-LIKE CARBON PROTECTIVE COATING FOR MAGNETIC RECORDING MEDIA DEVICES	GRILL, ALFRED
<u>08577165</u>	5712759	150	12/22/1995	SIDEWALL CAPACITOR WITH L-SHAPED DIELECTRIC	GRILL, ALFRED
<u>08577178</u>	5914851	150	12/22/1995	ISOLATED SIDEWALL CAPACITOR	GRILL, ALFRED
<u>08596909</u>	5869880	150	03/13/1996	STRUCTURE AND FABRICATION METHOD FOR STACKABLE, AIR-GAP-CONTAINING LOW EPSILON DIELECTRIC LAYERS	GRILL, ALFRED
<u>08608893</u>	5942328	150	02/29/1996	LOW DIELECTRIC CONSTANT AMORPHOUS FLUORINATED CARBON AND METHOD OF PREPARATION	GRILL, ALFRED
<u>08631239</u>	5679269	150	04/12/1996	DIAMOND-LIKE CARBON FOR USE IN VLSI AND ULSI	GRILL, ALFRED

				INTERCONNECT SYSTEMS	
<u>08636456</u>	5789320	150	04/23/1996	PLATING OF NOBLE METAL ELECTRODES FOR DRAM AND FRAM	GRILL, ALFRED
<u>08636624</u>	5757612	150	04/23/1996	STRUCTURE AND FABRICATION METHOD FOR NON-PLANAR MEMORY ELEMENTS	GRILL, ALFRED
<u>08646583</u>	5776823	150	05/08/1996	TASIN OXYGEN DIFFUSION BARRIER IN MULTILAYER STRUCTURES	GRILL, ALFRED
<u>08668241</u>	5796166	150	06/21/1996	TASIN OXYGEN DIFFUSION BARRIER IN MULTILAYER STRUCTURES	GRILL, ALFRED
<u>08798684</u>	5963397	150	02/12/1997	CERAMIC SUSPENSION BENT BY STRESSED PATCH	GRILL, ALFRED
<u>08805403</u>	6188120	150	02/24/1997	METHOD AND MATERIALS FOR THROUGH-MASK ELECTROPLATING AN SELECTIVE BASEREMOVAL	GRILL, ALFRED
<u>08866459</u>	5932907	150	05/30/1997	METHOD, MATERIALS, AND STRUCTURES FOR NOBLE METAL ELECTRODE CONTACTS TO SILICON	GRILL, ALFRED
<u>08866460</u>	Not Issued	161	05/30/1997	OXIDATION-RESISTANT SILICIDES FOR BARRIER LAYERS	GRILL, ALFRED
<u>08868772</u>	6428894	150	06/04/1997	TUNABLE AND REMOVABLE PLASMA DEPOSITED ANTIREFLECTIVE COATINGS	GRILL, ALFRED
<u>08899099</u>	Not Issued	161	07/24/1997	STRUCTURE AND FABRICATION METHOD FOR NON-PLANAR MEMORY ELEMENTS	GRILL, ALFRED
<u>08908295</u>	6131258	150	08/07/1997	SIDEWALL CAPACITOR WITH L-SHAPED DIELECTRIC	GRILL, ALFRED
<u>08910179</u>	6027966	150	08/13/1997	ISOLATED SIDEWALL CAPACITOR	GRILL, ALFRED
<u>08916001</u>	6030904	150	08/21/1997	STABILIZATION OF LOW-K CARBON-BASED DIELECTRICS	GRILL, ALFRED
<u>08924476</u>	Not Issued	161	08/25/1997	LAYERED RESIST SYSTEM USING TUNABLE AMORPHOUS CARBON FILM AS A BOTTOM LAYER AND METHODS OF FABRICATION THEREOF	GRILL, ALFRED
<u>08972993</u>	5945155	150	11/19/1997	LOW DIELECTRIC CONSTANT AMORPHOUS FLUORINATED	GRILL, ALFRED

CARBON AND METHOD OF PREPARATION					
<u>08974081</u>	<u>5942769</u>	150	11/19/1997	LOW DIELECTRIC CONSTANT AMORPHOUS FLUORINATED CARBON AND METHOD OF PREPARATION	GRILL, ALFRED
<u>09058651</u>	<u>5981000</u>	150	04/10/1998	METHOD FOR FABRICATING A THERMALLY STABLE DIAMOND-LIKE CARBON FILM	GRILL, ALFRED
<u>09067439</u>	<u>6448655</u>	150	04/28/1998	STABILIZATION OF FLUORINE-CONTAINING LOW-K DIELECTRICS IN A METAL/INSULATOR WIRING STRUCTURE BY ULTRAVIOLET IRRADIATION	GRILL, ALFRED
<u>09107567</u>	<u>6147009</u>	150	06/29/1998	HYDROGENATED OXIDIZED SILICON CARBON MATERIAL	GRILL, ALFRED
<u>09126212</u>	<u>6140226</u>	150	07/30/1998	DUAL DAMASCENE PROCESSING FO SEMICONDUCTOR CHIP INTERCONNECTS	GRILL, ALFRED
<u>09132608</u>	<u>6265779</u>	150	08/11/1998	METHOD AND MATERIAL FOR INTEGRATION OF FUORINE-CONTAINING LOW-K DIELECTRICS	GRILL, ALFRED
<u>09139367</u>	Not Issued	161	08/25/1998	LITHOGRAPHIC STRUCTURES HAVING INDEX OF REFRACTION AND EXTINCTION COFFICIENTS PROFILES FOR CONTROLLING REFLECTION TO CONTROL UNEWIDTH VARIATION	GRILL, ALFRED
<u>09192133</u>	<u>6017814</u>	150	11/13/1998	STRUCTURE AND FABRICATION METHOD FOR STACKABLE, AIR-GAP-CONTAINING LOW EPSILON DIELECTRIC LAYERS	GRILL, ALFRED
<u>09281208</u>	<u>6049443</u>	150	03/30/1999	SUSPENSION BENT BY STRESSED PATCH	GRILL, ALFRED
<u>09303595</u>	<u>6242321</u>	150	05/03/1999	STRUCTURE AND FABRICATION METHOD FOR NON-PLANAR MEMORY ELEMENTS	GRILL, ALFRED

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Inventor Name Search Result

Your Search was:

Last Name = OTT

First Name = JOHN ALBRECHT

Application#	Patent#	Status	Date Filed	Title	Inventor Name
08951827	5963817	150	10/16/1997	BULK AND STRAINED SILICON ON INSULATOR USING LOCAL SELECTIVE OXIDATION	OTT, JOHN ALBRECHT
09290778	6251751	150	04/13/1999	BULK AND STRAINED SILICON ON INSULATOR USING LOCAL SELECTIVE OXIDATION	OTT, JOHN ALBRECHT

Inventor Search Completed: No Records to Display.

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Inventor Name Search Result

Your Search was:

Last Name = MEYERSON

First Name = BERNARD

Application#	Patent#	Status	Date Filed	Title	Inventor Name
<u>06394018</u>	<u>4436797</u>	150	06/30/1982	X-RAY MASK	MEYERSON, BERNARD S.
<u>06481538</u>	<u>4526593</u>	150	04/04/1983	RESTRICTOR PLUG DEVICE WITH FILTER FOR A GAS SUPPLY SYSTEM	MEYERSON, BERNARD S.
<u>06559583</u>	<u>4504331</u>	150	12/08/1983	SILICON DOPANT SURCE IN INTERMETALLIC SEMICONDUCTOR GROWTH OPERATIONS	MEYERSON, BERNARD S.
<u>06567303</u>	Not Issued	166	12/30/1983	METHOD FOR PRODUCING HIGH ENERGY ELECTROLUMINESCENT DEVICES	MEYERSON, BERNARD S.
<u>06626504</u>	<u>4592933</u>	150	06/29/1984	HIGH EFFICIENCY HOMOGENEOUS CHEMICAL VAPOR DEPOSITION	MEYERSON, BERNARD S.
<u>06793517</u>	<u>4647494</u>	150	10/31/1985	SILICON/CARBON PROTECTION OF METALLIC MAGNETIC STRUCTURES	MEYERSON, BERNARD S.
<u>06895119</u>	<u>4684542</u>	150	08/11/1986	LOW PRESSURE CHEMICAL VAPOR DEPOSITION OF TUNGSTEN SILICIDE	MEYERSON, BERNARD S.
<u>06906854</u>	Not Issued	166	09/12/1986	METHOD AND APPARATUS FOR LOW TEMPERATURE, LOW PRESSURE CHEMICAL VAPOR DEPOSITION OF EPITAXIAL SILICON LAYERS	MEYERSON, BERNARD S.
<u>06921985</u>	Not Issued	166	10/22/1986	METHOD FOR PRODUCING HIGH ENERGY ELECTROLUMINESCENT DEVICES	MEYERSON, BERNARD S.
<u>07171603</u>	<u>4972246</u>	250	03/22/1988	EFFECTIVE NARROW BAND GAP BASE TRANSISTOR	MEYERSON, BERNARD S.
<u>07307154</u>	<u>5151383</u>	150	02/06/1989	METHOD FOR PRODUCING HIGH ENERGY ELECTROLUMINESCENT DEVICES	MEYERSON, BERNARD S.

<u>07327627</u>	Not Issued	166	03/24/1989	SEMICONDUCTOR DEVICE WITH SELF-ALIGNED CONTACT TO BURIED SUBCOLLECTOR	MEYERSON, BERNARD S.
<u>07342630</u>	Not Issued	166	04/19/1989	METHOD AND APPARATUS FOR LOW TEMPERATURE, LOW PRESSURE CHEMICAL VAPOR DEPOSITION OF EPITAXIAL SILICON LAYERS	MEYERSON, BERNARD S.
<u>07405508</u>	5008207	150	09/11/1989	METHOD OF FABRICATING A NARROW BASE TRANSISTOR	MEYERSON, BERNARD S.
<u>07427679</u>	Not Issued	161	10/26/1989	THREE-DIMENSIONAL SEMICONDUCTOR STRUCTURES FORMED FROM PLANAR LAYERS	MEYERSON, BERNARD S.
<u>07504496</u>	5031029	250	04/04/1990	COPPER DEVICE AND USE THEREOF WITH SEMICONDUCTOR DEVICES	MEYERSON, BERNARD S.
<u>07531218</u>	5316958	150	05/31/1990	METHOD OF DOPANT ENHANCEMENT IN AN EPITAXIAL SILICON LAYER USING GERMANIUM	MEYERSON, BERNARD S.
<u>07537180</u>	5181964	150	06/13/1990	SINGLE ENDED ULTRA-HIGH VACUUM CHEMICAL VAPOR DEPOSITION (UHV/CVD) REACTOR	MEYERSON, BERNARD S.
<u>07622309</u>	Not Issued	166	12/05/1990	METHOD AND APPARATUS FOR LOW TEMPERATURE, LOW PRESSURE CHEMICAL VAPOR DEPOSITION OF EPITAXIAL SILICON LAYERS	MEYERSON, BERNARD S.
<u>07624018</u>	5117271	150	12/07/1990	LOW CAPACITANCE BIPOLAR JUNCTION TRANSISTOR AND FABRICATION PROCESS THEREFOR	MEYERSON, BERNARD S.
<u>07634671</u>	5159508	150	12/27/1990	MAGNETIC HEAD SLIDER HAVING A PROTECTIVE COATING THEREIN	MEYERSON, BERNARD S.
<u>07639625</u>	Not Issued	166	01/10/1991	GRADED CHANNEL FIELD EFFECT TRANSISTOR	MEYERSON, BERNARD S.
<u>07643966</u>	Not Issued	169	01/22/1991	GRADED CHANNEL FIELD EFFECT TRANSISTOR	MEYERSON, BERNARD S.
<u>07648797</u>	5132765	150	01/31/1991	NARROW BASE TRANSISTOR AND METHOD OF FABRICATING SAME	MEYERSON, BERNARD S.
<u>07656902</u>	5160987	250	02/15/1991	THREE-DIMENSIONAL SEMICONDUCTOR STRUCTURES	MEYERSON, BERNARD S.

FORMED FROM PLANAR LAYERS					
<u>07664681</u>	5119157	150	03/05/1991	SEMICONDUCTOR DEVICE WITH SELF-ALIGNED CONTACT TO BURIED SUBCOLLECTOR	MEYERSON, BERNARD S.
<u>07678390</u>	5057450	150	04/01/1991	METHOD FOR FABRICATING SILICON-ON-INSULATOR STRUCTURES	MEYERSON, BERNARD S.
<u>07709921</u>	Not Issued	166	05/31/1991	LOW DEFECT DENSITY/ARBITRARY LATTICE CONSTANT HETEROEPITAXIAL LAYERS	MEYERSON, BERNARD S.
<u>07715731</u>	Not Issued	161	06/17/1991	SEMICONDUCTOR DEVICE WITH SELF-ALIGNED CONTACT TO BURIED SUBCOLLECTOR	MEYERSON, BERNARD S.
<u>07723091</u>	Not Issued	166	06/28/1991	FABRICATION OF DEFECT FREE SILICON ON AN INSULATING SUBSTRATE AND METHOD OF FORMING SAME IN THE CLAIMS	MEYERSON, BERNARD S.
<u>07774010</u>	5273829	250	10/08/1991	EPITAXIAL SILICON MEMBRANES	MEYERSON, BERNARD S.
<u>07784280</u>	5246884	150	10/30/1991	CVD DIAMOND OR DIAMOND-LIKE CARBON FOR CHEMICAL-MECHANICAL POLISH ETCH STOP	MEYERSON, BERNARD S.
<u>07785547</u>	Not Issued	166	10/31/1991	GRADED CHANNEL FIELD EFFECT TRANSISTOR	MEYERSON, BERNARD S.
<u>07792493</u>	5352912	150	11/13/1991	GRADED BANDGAP SINGLE-CRYSTAL Emitter HETEROJUNCTION BIPOLAR TRANSISTOR	MEYERSON, BERNARD S.
<u>07841192</u>	5298452	150	02/21/1992	METHOD AND APPARATUS FOR LOW TEMPERATURE, LOW PRESSURE CHEMICAL VAPOR DEPOSITION OF EPITAXIAL SILICON LAYERS	MEYERSON, BERNARD S.
<u>07868371</u>	5241131	250	04/14/1992	EROSION/CORROSION RESISTANT DIAPHRAGM	MEYERSON, BERNARD S.
<u>07900870</u>	Not Issued	161	06/18/1992	ULTRA HIGH DENSITY THREE-DIMENSIONAL SEMICONDUCTOR STRUCTURES	MEYERSON, BERNARD S.
<u>07927901</u>	5461250	150	08/10/1992	SIGE THIN FILM OR SOI MOSFET AND METHOD FOR MAKING THE SAME	MEYERSON, BERNARD S.
<u>07968731</u>	Not	161	10/30/1992	SUPERLATTICE Emitter	MEYERSON,

	Issued			BIPOLAR TRANSISTOR	BERNARD S.
<u>07985344</u>	5821577	150	11/30/1992	GRADED CHANNEL FIELD EFFECT TRANSISTOR	MEYERSON, BERNARD S.
<u>08012812</u>	5319240	150	02/03/1993	THREE DIMENSIONAL INTEGRATED DEVICE AND CIRCUIT STRUCTURES	MEYERSON, BERNARD S.
<u>08071767</u>	5409852	150	07/21/1993	METHOD OF MANUFACTURING THREE DIMENSIONAL INTERGRATED DEVICE AND CIRCUIT STRUCTURES	MEYERSON, BERNARD S.
<u>08120290</u>	5357899	250	09/13/1993	EPITAXIAL SILICON MEMBRANES	MEYERSON, BERNARD S.
<u>08126125</u>	6004137	150	09/23/1993	METHOD FOR MAKING GRADED CHANNEL FIELD EFFECT TRANSISTOR	MEYERSON, BERNARD S.
<u>08171371</u>	Not Issued	166	12/22/1993	LOW DEFECT DENSITY/ARBITRARY LATTICE CONSTANT HETEROEPITAXIAL LAYERS	MEYERSON, BERNARD S.
<u>08186195</u>	5607511	150	01/24/1994	METHOD AND APPARATUS FOR LOW TEMPERATURE, LOW PRESSURE CHEMICAL VAPOR DEPOSITION OF EPITAXIAL SILICON LAYERS	MEYERSON, BERNARD S.
<u>08223098</u>	5540785	150	04/04/1994	FABRICATION OF DEFECT FREE SILICON ON AN INSULATING SUBSTRATE	MEYERSON, BERNARD S.
<u>08225499</u>	5462883	150	04/11/1994	METHOD OF FABRICATING DEFECT-FREE SILICON ON AN INSULATING SUBSTRATE	MEYERSON, BERNARD S.
<u>08472037</u>	5810924	150	06/07/1995	LOW DEFECT DENSITY/ARBITRARY LATTICE CONSTANT HETEROEPITAXIAL LAYERS	MEYERSON, BERNARD S.
<u>08474209</u>	5659187	150	06/07/1995	LOW DEFECT DENSITY/ARBITRARY LATTICE CONSTANT HETEROEPITAXIAL LAYERS	MEYERSON, BERNARD S.

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